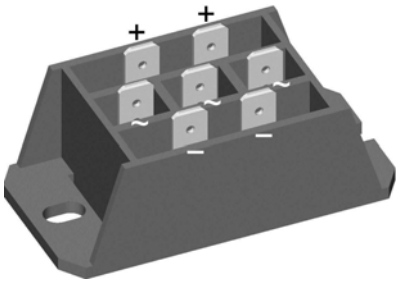
Standard Rectifier Module

3~ Rectifier		
V_{RRM}	=	1600 V
I_{DAV}	=	75 A
I_{FSM}	=	700 A

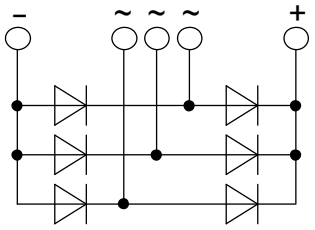
3~ Rectifier Bridge

Part number

VUO60-16NO3



E72873



Features / Advantages:

- Package with DCB ceramic
- Reduced weight
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: FO-F-B

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- ¼" fast-on terminals
- Easy to mount with two screws
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

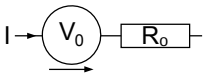
Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1700	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1600	V
I_R	*reverse current*	V_R = 1600 V	T_{VJ} = 25°C			100	µA
		V_R = 1600 V	T_{VJ} = 150°C			1.5	mA
V_F	*forward voltage drop*	I_F = 25 A	T_{VJ} = 25°C			1.06	V
		I_F = 75 A				1.30	V
		I_F = 25 A	T_{VJ} = 125°C			0.96	V
		I_F = 75 A				1.27	V
I_{DAV}	*bridge output current*	T_C = 110°C	T_{VJ} = 150°C			75	A
		rectangular d = ⅓					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			0.77	V
r_F	*slope resistance* }					6.5	mΩ
R_{thJC}	*thermal resistance junction to case*					1.2	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.4		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			100	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			700	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			755	A
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			595	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			645	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			2.45	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			2.37	kA²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			1.77	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.73	kA²s
C_J	*junction capacitance*	V_R = 400 V; f = 1 MHz	T_{VJ} = 25°C		25		pF

Package FO-F-B					Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal					100	A
T_{stg}	*storage temperature*				-40		125	°C
T_{VJ}	*virtual junction temperature*				-40		150	°C
Weight						45		g
M_D	*mounting torque*				2		2.5	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	18.0	6.0			mm
$d_{Spb/Apb}$			*terminal to backside*	26.0	20.0			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA		3600			V
		t = 1 minute			3000			V

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO60-16NO3	VUO60-16NO3	Box	10	465348

Equivalent Circuits for Simulation

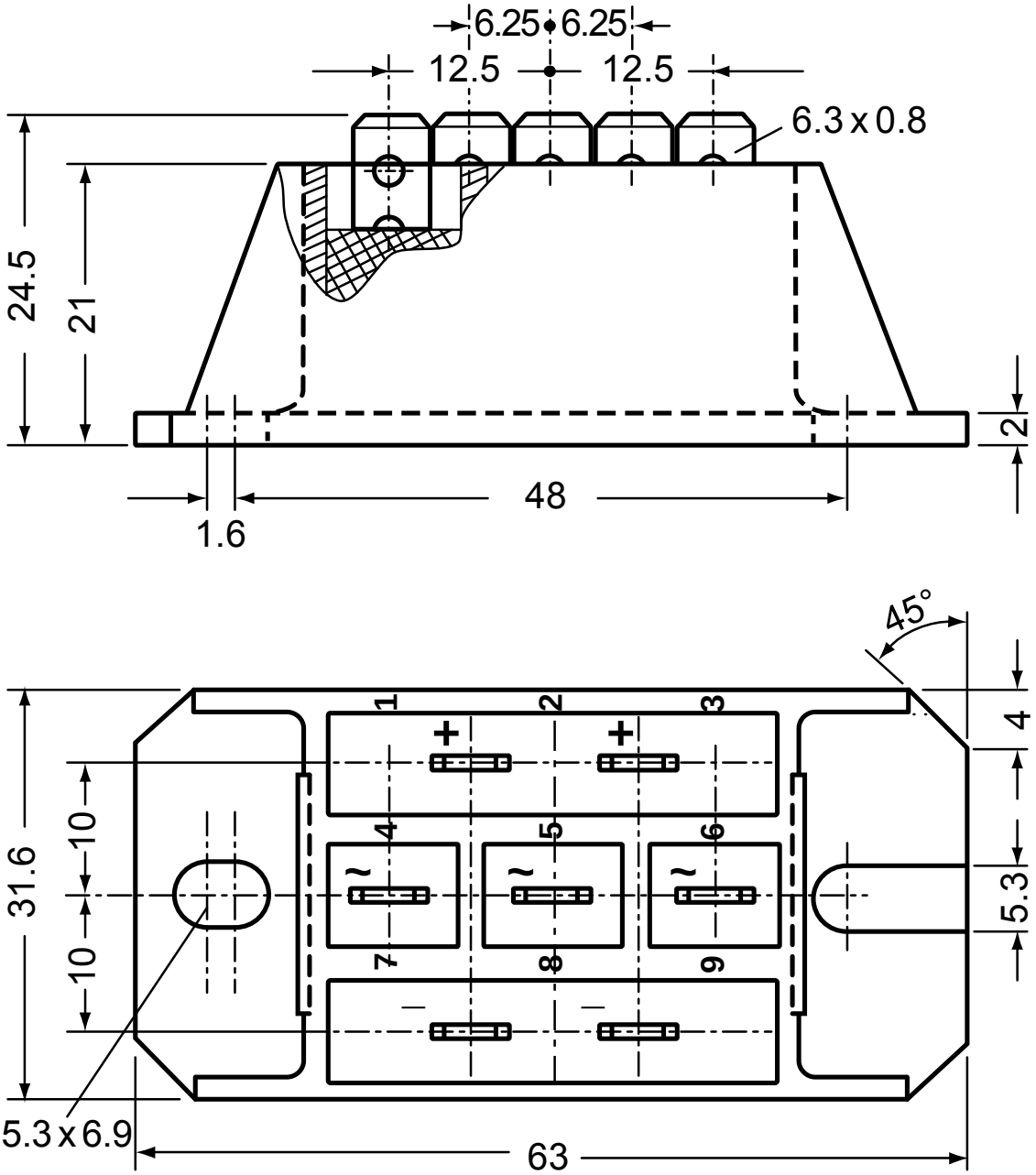
** on die level* T_{VJ} = 150 °C

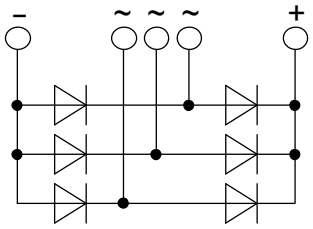


Rectifier

$V_{0\,max}$	*threshold voltage*	0.77	V
$R_{0\,max}$	*slope resistance **	5.3	mΩ

Outlines FO-F-B





Rectifier

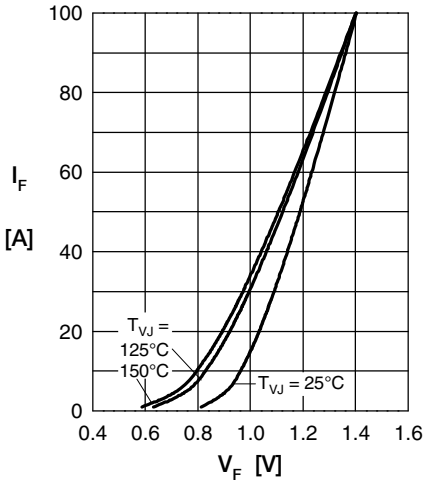


Fig. 1 Forward current vs. voltage drop per diode

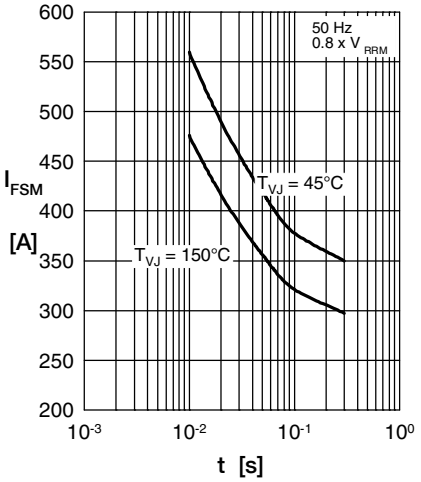


Fig. 2 Surge overload current vs. time per diode

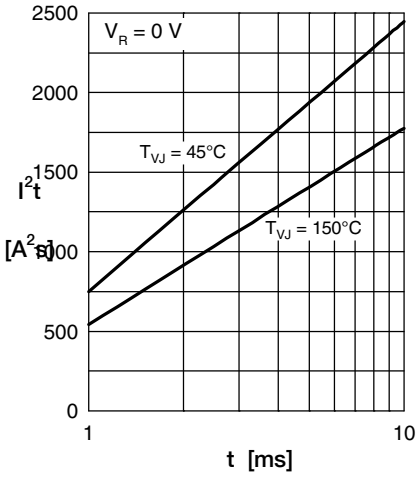


Fig. 3 I^2t vs. time per diode

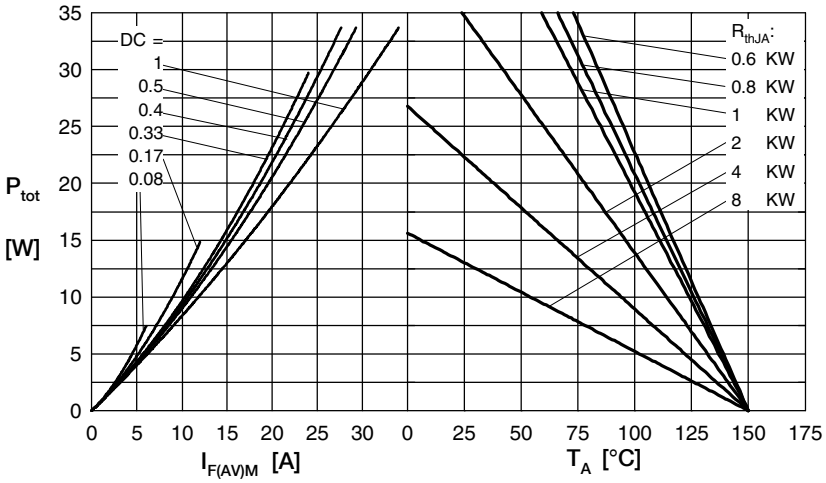


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

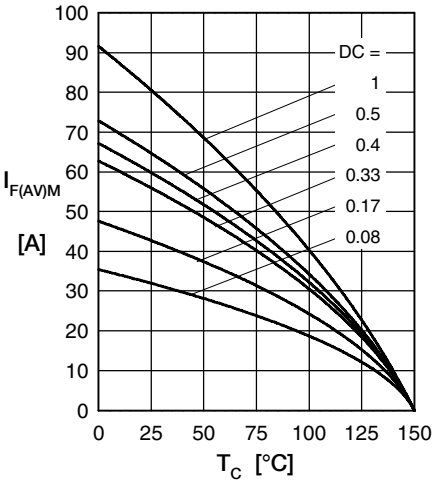


Fig. 5 Max. forward current vs. case temperature per diode

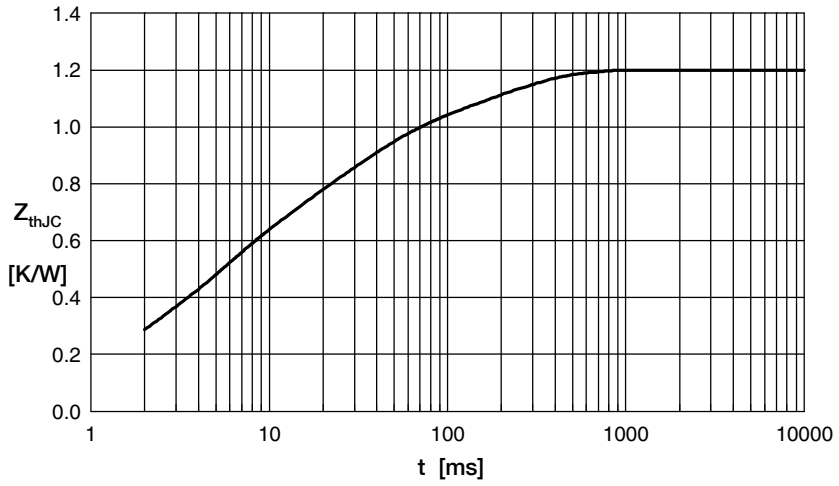


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.0607	0.00040
2	0.1330	0.00256
3	0.3305	0.00450
4	0.4130	0.02420
5	0.2628	0.18000